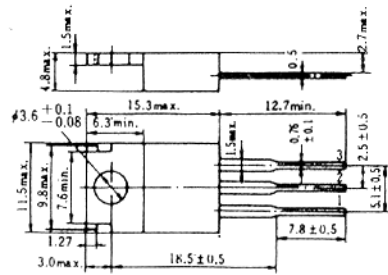
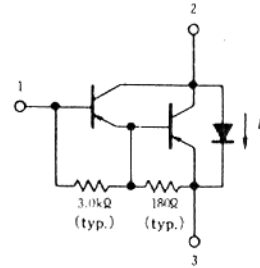


2SB1106

SILICON PNP TRIPLE DIFFUSED
LOW FREQUENCY POWER AMPLIFIER



1. Base
2. Collector (Flange)
3. Emitter (Dimensions in mm)



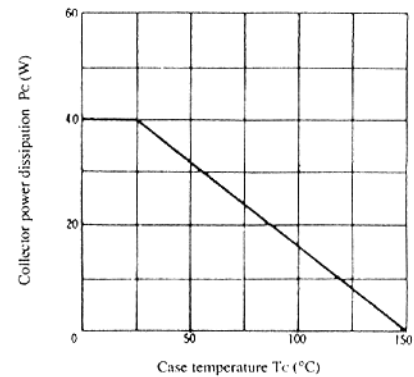
(JEDEC TO-220AB)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SB1106	Unit
Collector to base voltage	V _{CBO}	-120	V
Collector to emitter voltage	V _{CEO}	-120	V
Emitter to base voltage	V _{EBO}	-7	V
Collector current	I _C	-6	A
Collector peak current	i _{C(peak)}	-12	A
Collector power dissipation	P _C *	40	W
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C
C to E diode forward current	I _D *	6	A

* Value at T_C = 25°C

MAXIMUM COLLECTOR DISSIPATION CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to emitter breakdown voltage	V _{(BR)CEO}	I _C = -25mA, R _{BE} = ∞	-120	—	—	V
Emitter to base breakdown voltage	V _{(BR)EBO}	I _E = -50mA, I _C = 0	-7	—	—	V
Collector cutoff current	I _{CBO}	V _{CB} = -120V, I _E = 0	—	—	-100	μA
	I _{CEO}	V _{CE} = -100V, R _{BE} = ∞	—	—	-10	μA
DC current transfer ratio	h _{FE}	V _{CE} = -3V, I _C = -3A*	1000	—	20000	
Collector to emitter saturation voltage	V _{CE(sat)1}	I _C = -3A, I _B = -6mA*	—	—	-1.5	V
	V _{CE(sat)2}	I _C = -6A, I _B = -60mA*	—	—	-3.0	V
Base to emitter saturation voltage	V _{BE(sat)1}	I _C = -3A, I _B = -6mA*	—	—	-2.0	V
	V _{BE(sat)2}	I _C = -6A, I _B = -60mA*	—	—	-3.5	V
C to E diode forward voltage	V _D	I _D = 6A*	—	—	3.0	V
Turn on time	t _{on}	I _C = -3A, I _{B1} = -I _{B2} = -6mA	—	0.5	—	μs
Storage time	t _{stg}		—	3.0	—	μs
Fall time	t _f		—	1.0	—	μs

* Pulse Test

